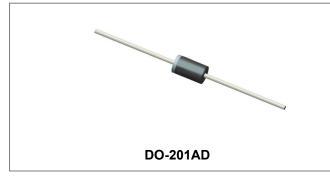






HER301G-HER308G HIGH EFFICIENCY GLASS PASSIVATED RECTIFIER



Features

- · Low power loss, high efficiency
- Low leakage
- Low forward voltage drop
- High current capability
- High speed switching
- High reliability
- High current surge
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

Case: DO-201AD Molded plastic

• Epoxy: UL94V-0 rate flame retardant

Lead: MIL-STD-202E method 208C guaranteed

Mounting Position: AnyWeight: 1.02 gram

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

	SYMBO LS	HER 301G	HER 302G	HER 303G	HER 304G	HER 305G	HER 306G	HER 307G	HER 308G	Units
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	300	400	600	800	1000	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at $T_A \! = \! 50 ^{\circ}\! \mathrm{C}$	I _(AV)	3.0				А				
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	125			А					
Maximum instantaneous forward voltage at 3.0A	V _F	1.0 1.30 1.70				V				
Maximum DC reverse current T_A =25 $^{\circ}$ C at rated DC blocking voltage T_A =100 $^{\circ}$ C	I _R	5.0 150				μА				
Maximum reverse recovery time (Note 1)	t _{rr}	50 75			ns					
Typical junction capacitance (Note 2)	CJ	70 50			pF					
Typical thermal resistance (Note 3)	R _{θJA}	20				°C/W				
Operating junction and storage temperature range	T _J ,T _{STG}	-65 to +150				°C				

- Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A. Irr=0.25A
 - 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 - 3. Thermal resistance from junction to ambient at 0.375"(9.5mm) lead length, P.C.B mounted.
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Ratings and Characteristics Curves

FIG. 1- FORWARD CURRENT DERATING CURVE

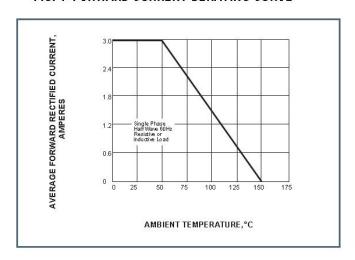


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

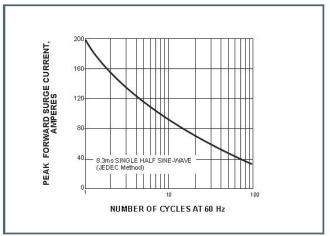


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

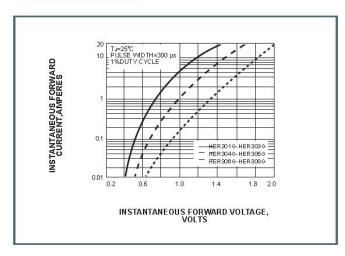
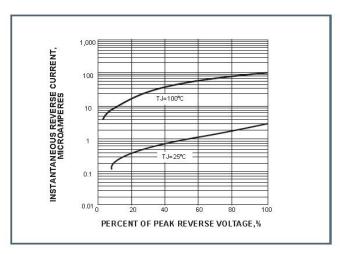


FIG. 4-TYPICAL REVERSE CHARACTERISTICS



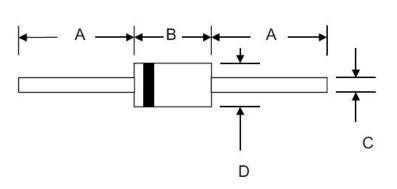
[•] China - Germany - Korea - Singapore - United States •







Mechanical Dimensions DO-201AD



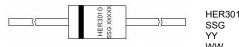
CYMPOL	Millim	neters	Inches			
SYMBOL	Min. Max.		Min.	Max.		
Α	25.4	-	1.000	-		
В	8.50	9.50	0.335	0.374		
С	1.2	1.3	0.048	0.052		
D	5.0	5.6	0.197	0.220		

Ordering Information

Device	Package	Shipping
HER301G THRU HER308G	DO-201AD (Pb-Free)	1250pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

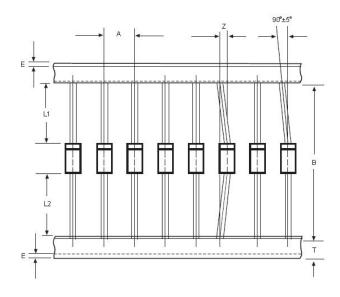
Marking Diagram



Where XXXXX is YYWWL

HER301G = Part Name SSG = SSG YY = Year WW = Week L = Lot Number

Carrier Tape Specification DO-201AD



SYMBOL	Millimeters				
	Min.	Max.			
А	9.50	10.50			
В	50.9	53.9			
Z	-	1.20			
Т	5.60	6.40			
E	-	0.80			
IL1-L2I	-	1.0			

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